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STTH60W03C

Turbo 2 ultrafast high voltage rectifier

Datasheet – production data

Features

- Ultrafast switching
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses
- ECOPACK[®]2 compliant component

Description

The STTH60W03C uses ST Turbo 2 300 V technology. It is especially suited to be used for DC/DC and DC/AC converters in secondary stage of MIG/MMA/TIG welding machine. Housed in ST's TO-247, this device offers high power integration for all welding machines and industrial applications.

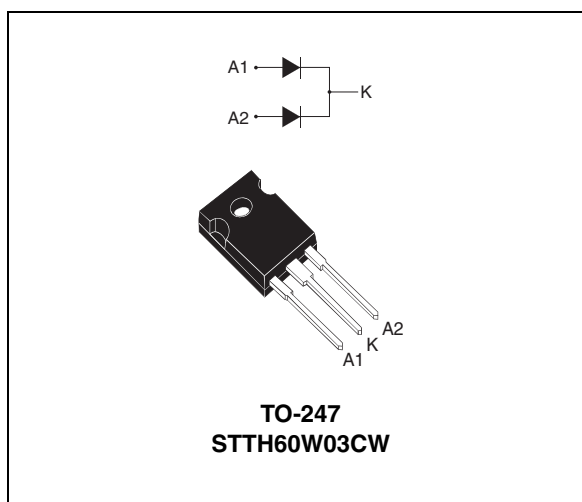


Table 1. Device summary

Symbol	Value
$I_{F(AV)}$	2 x 30 A
V_{RRM}	300 V
t_{rr} (typ)	25 ns
T_j	175 °C
V_F (typ)	0.94 V

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Table 2. Absolute ratings (limiting values, at 25 °C, unless otherwise specified)

Symbol	Parameter	Value	Unit	
V _{RRM}	Repetitive peak reverse voltage	300	V	
I _{F(RMS)}	RMS forward current	50	A	
I _{F(AV)}	Average forward current, δ = 0.5	T _c = 110 °C Per diode	30	A
		T _c = 95 °C Per device	60	
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms sinusoidal	280	A
T _{stg}	Storage temperature range	-65 to + 175	°C	
T _j	Maximum operating junction temperature	+ 175	°C	

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit	
R _{th(j-c)}	Junction to case	Per diode	1.5	°C / W
		Total	0.9	°C / W
R _{th(c)}	Coupling	0.3	°C / W	

When diodes 1 and 2 are used simultaneously:

$$T_{j(\text{diode } 1)} = P_{(\text{diode } 1)} \times R_{th(j-c)}(\text{Per diode}) + P_{(\text{diode } 2)} \times R_{th(c)}$$

Table 4. Static electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ	Max.	Unit
I _R ⁽¹⁾	Reverse leakage current	T _j = 25 °C	V _R = V _{RRM}		20	μA
		T _j = 125° C		20	200	
V _F ⁽²⁾	Forward voltage drop	T _j = 25° C	I _F = 30 A		1.45	V
		T _j = 150 °C		0.94	1.15	
		T _j = 25° C	I _F = 60 A		1.7	
		T _j = 150° C		1.18	1.45	

1. Pulse test: t_p = 5 ms, δ < 2%

2. Pulse test: t_p = 380 μs, δ < 2%

To evaluate the conduction losses use the following equation:

$$P = 0.85 \times I_{F(AV)} + 0.01 I_{F(RMS)}^2$$

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Table 5. Dynamic electrical characteristics

Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
I_{RM}	Reverse recovery current	$T_j = 125\text{ }^\circ\text{C}$	$I_F = 30\text{ A}, V_R = 200\text{ V}$ $di_F/dt = -200\text{ A}/\mu\text{s}$		7	9	A
Q_{RR}	Reverse recovery charge				180		nC
S_{factor}	Softness factor				0.3		
t_{rr}	Reverse recovery time	$T_j = 25\text{ }^\circ\text{C}$	$I_F = 1\text{ A}, V_R = 30\text{ V}$ $di_F/dt = -100\text{ A}/\mu\text{s}$		25	35	ns
t_{fr}	Forward recovery time	$T_j = 25\text{ }^\circ\text{C}$	$I_F = 30\text{ A}, V_{FR} = 1.5\text{ V}$ $di_F/dt = 200\text{ A}/\mu\text{s}$			180	ns
V_{FP}	Forward recovery voltage				2.0	3.0	V

Figure 1. Average forward power dissipation versus average forward current (per diode)

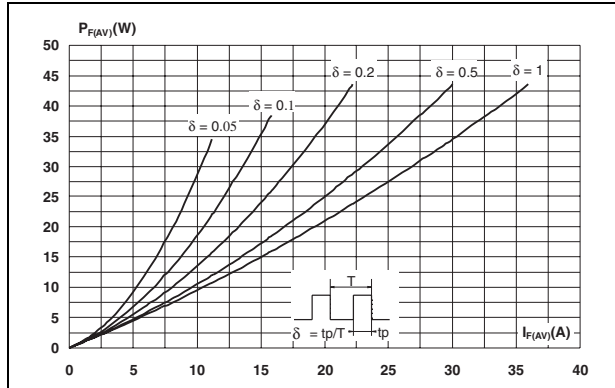


Figure 2. Forward voltage drop versus forward current (per diode)

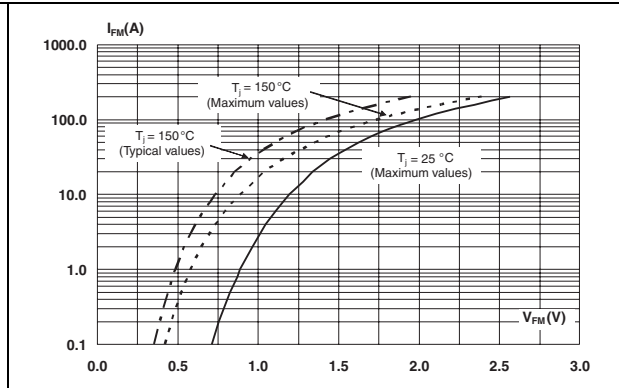


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

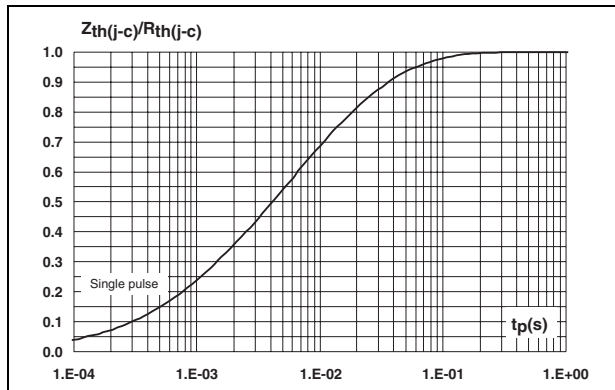
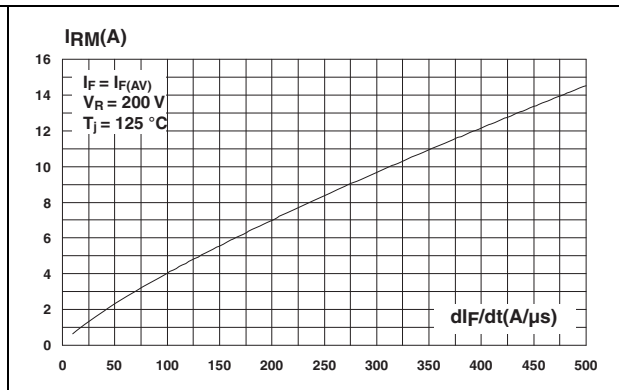


Figure 4. Peak reverse recovery current versus di_F/dt (typical values, per diode)



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Figure 5. Reverse recovery time versus di_F/dt (typical values, per diode)

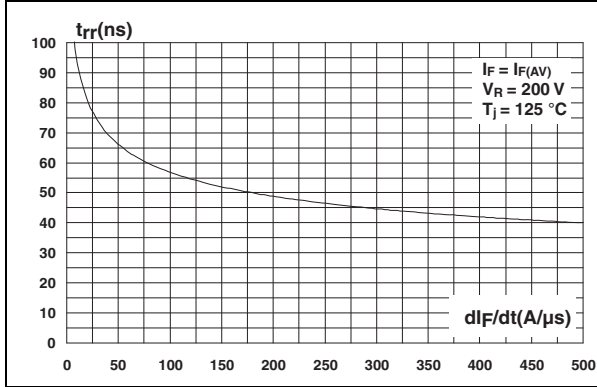


Figure 6. Reverse recovery charges versus di_F/dt (typical values, per diode)

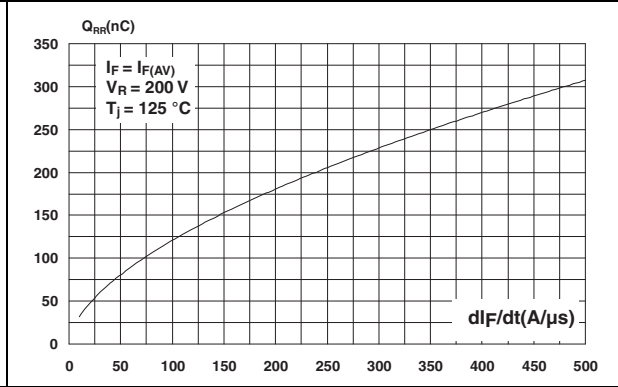


Figure 7. Relative variations of dynamic parameters versus junction temperature

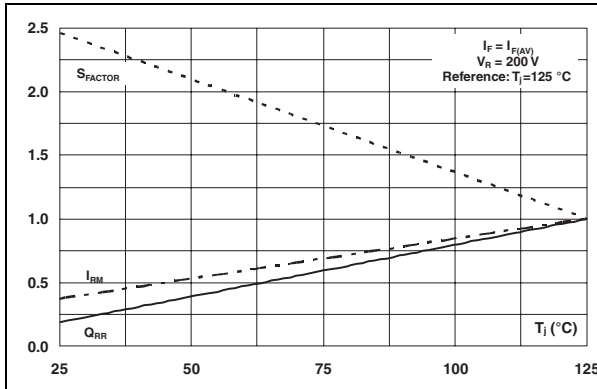
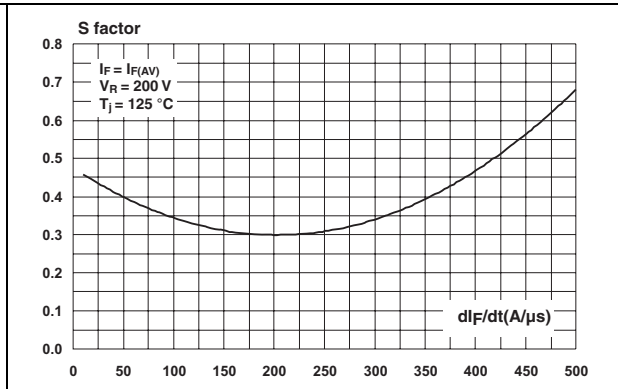


Figure 8. Reverse recovery softness factor versus di_F/dt (typical values, per diode)



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Figure 9. Forward recovery time versus di_F/dt (typical values, per diode)

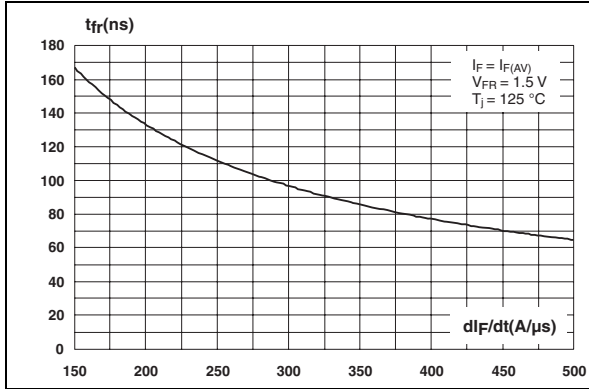


Figure 10. Transient peak forward voltage versus di_F/dt (typical values, per diode)

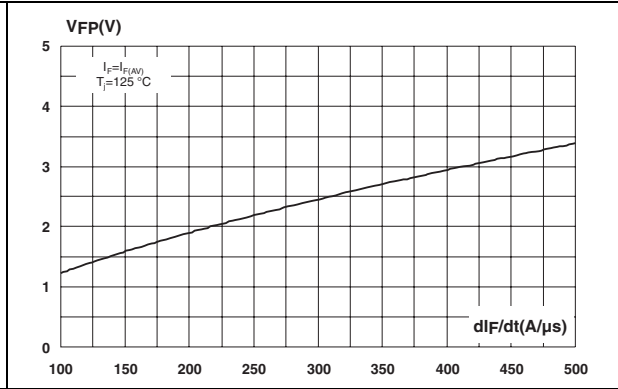
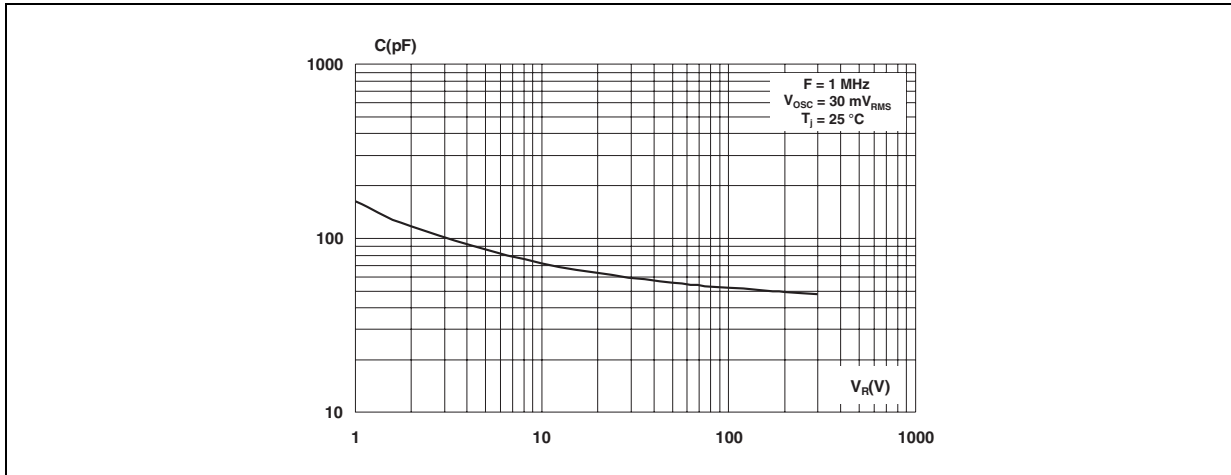


Figure 11. Junction capacitance versus reverse voltage applied (typical values, per diode)



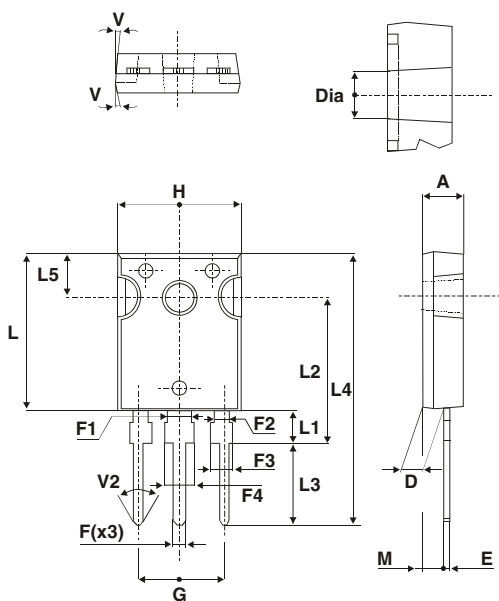
2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 N·m (1.0 N·m maximum)

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 6. TO-247 dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.85	5.15	0.191	0.203
D	2.20	2.60	0.086	0.102
E	0.40	0.80	0.015	0.031
F	1.00	1.40	0.039	0.055
F1	3.00 typ.		0.118 typ.	
F2	2.00 typ.		0.078 typ.	
F3	2.00	2.40	0.078	0.094
F4	3.00	3.40	0.118	0.133
G	10.90 typ.		0.429 typ.	
H	15.45	15.75	0.608	0.620
L	19.85	20.15	0.781	0.793
L1	3.70	4.30	0.145	0.169
L2	18.50 typ.		0.728 typ.	
L3	14.20	14.80	0.559	0.582
L4	34.60 typ.		1.362 typ.	
L5	5.50 typ.		0.216 typ.	
M	2.00	3.00	0.078	0.118
V	5° typ.		5° typ.	
V2	60° typ.		60° typ.	
Dia.	3.55	3.65	0.139	0.143



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Ordering information

3 Ordering information

Table 7. Ordering information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STTH60W03CW	STTH60W03CW	TO-247	4.46 g	50	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
07-June-2012	1	First issue.

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